EMBEDDED ORGANIC STOP LAYER FOR DUAL DAMASCENE PATTERNING

BACKGROUND OF THE INVENTION

ABSTRACT

A new method of forming a dual damascene interconnect structure, wherein damage of interconnect and contamination of dielectrics during etching is minimized by having an embedded organic stop layer over the lower interconnect and later etching the organic stop layer with an H2 containing plasma, or hydrogen radical.

(Figure 2A)

This Sheet Has Been Replaced